

BLF882; BLF882S

UHF power LDMOS transistor

Rev. 2 — 3 July 2015

Product data sheet

1. Product profile

1.1 General description

A 200 W LDMOS RF power transistor for broadcast transmitter applications and industrial applications. The transistor can deliver 200 W in broadband applications from HF to 860 MHz. The excellent ruggedness and broadband performance of this device makes it ideal for digital transmitter applications.

Table 1. Test information

RF performance at $T_{case} = 25\text{ °C}$ in a class-AB test circuit.

Test signal	f (MHz)	V _{DS} (V)	P _{L(AV)} (W)	G _p (dB)	η _D (%)	PAR (dB)
RF performance in a class-AB 705 MHz narrowband test circuit						
CW, class-AB	705	50	180	21	62	-
CW pulsed, class-AB	705	50	200	21	63	-
RF performance in a class-AB 470 MHz to 705 MHz broadband test circuit						
DVB-T (8k OFDM)	470 to 705	50	33	20	28 to 31	8.0 to 8.4 [1]

[1] PAR of output signal at 0.01% probability on CCDF; PAR of input signal = 9.5 dB at 0.01% probability on CCDF.

1.2 Features and benefits

- Integrated ESD protection
- Excellent ruggedness
- High power gain
- High efficiency
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

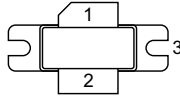
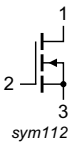
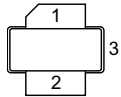
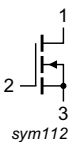
1.3 Applications

- Transmitter applications in the HF to 860 MHz frequency range
- Industrial applications in the HF to 860 MHz frequency range
- Broadcast transmitters



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF882 (SOT502A)			
1	drain		
2	gate		
3	source [1]		
BLF882S (SOT502B)			
1	drain		
2	gate		
3	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF882	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT502A
BLF882S	-	earless flanged ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	104	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 85\text{ °C}; P_L = 180\text{ W}$ [1]	0.56	K/W

[1] $R_{th(j-c)}$ is measured under RF conditions.

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 1.2\text{ mA}$	104	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 120\text{ mA}$	1.4	1.9	2.4	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$	-	-	1.4	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	-	19	-	A
I_{GSS}	gate leakage current	$V_{GS} = 10\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	140	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 4.25\text{ A}$	-	240	-	$\text{m}\Omega$

[1] I_D is the drain current

Table 7. AC characteristics

$T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $f = 1\text{ MHz}$	-	105	-	pF
C_{oss}	output capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $f = 1\text{ MHz}$	-	34	-	pF
C_{rs}	feedback capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $f = 1\text{ MHz}$	-	0.7	-	pF

Table 8. RF characteristics

Test signal: CW pulsed; RF characteristics in NXP production narrowband test circuit; $T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage		-	50	-	V
I_{Dq}	quiescent drain current		-	100	-	mA
$P_{L(AV)}$	average output power	$f = 705\text{ MHz}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 10\text{ }\%$	196	200	-	W
G_p	power gain		19.6	20.6	-	dB
η_D	drain efficiency		60	63	-	%

7. Test information

7.1 Ruggedness in class-AB operation

The BLF882 and BLF882S are capable of withstanding a load mismatch corresponding to $V_{SWR} \geq 20 : 1$ through all phases under the following conditions: $V_{DS} = 50\text{ V}$; $f = 705\text{ MHz}$ at rated $P_{L(1dB)}$.

7.2 Test circuit

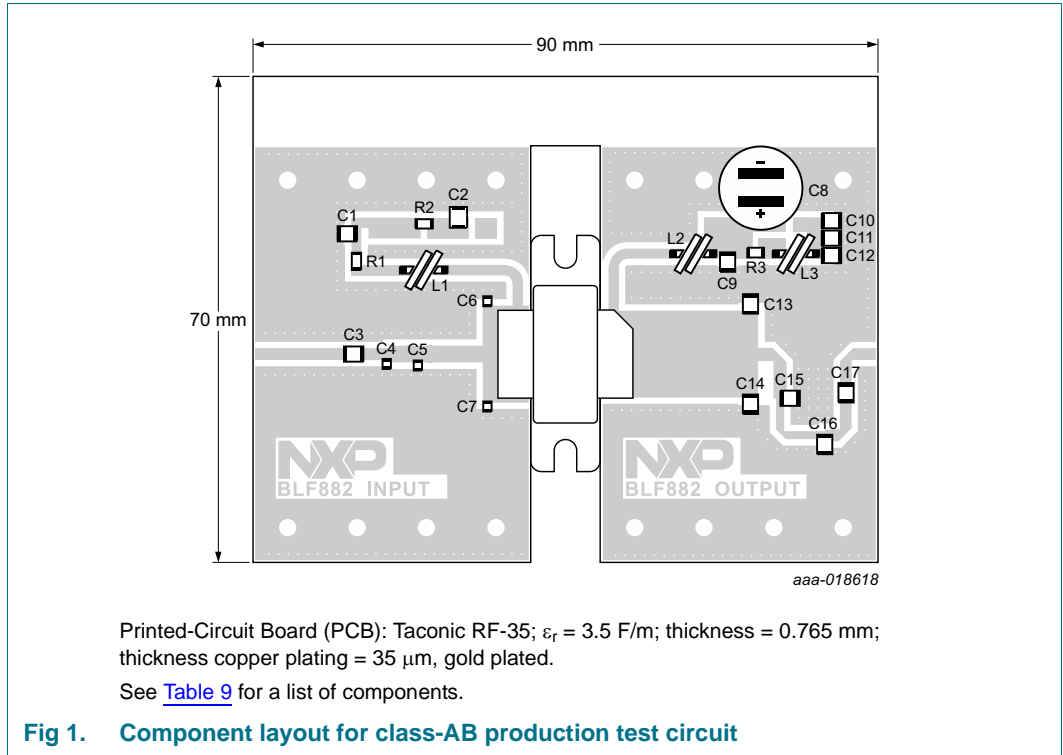


Table 9. List of components

For test circuit see [Figure 1](#).

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	62 pF	[1]
C2	multilayer ceramic chip capacitor	100 nF	
C3, C9	multilayer ceramic chip capacitor	56 pF	[1]
C4	multilayer ceramic chip capacitor	12 pF	[2]
C5	multilayer ceramic chip capacitor	11 pF	[2]
C6, C7	multilayer ceramic chip capacitor	24 pF	[2]
C8	electrolytic capacitor	220 μF	
C10, C11, C12	electrolytic capacitor	750 pF	[1]
C13	multilayer ceramic chip capacitor	16 pF	[3]
C14	multilayer ceramic chip capacitor	18 pF	[3]
C15	multilayer ceramic chip capacitor	5.6 pF	[3]
C16	multilayer ceramic chip capacitor	6.8 pF	[3]
C17	multilayer ceramic chip capacitor	56 pF	[3]
L1, L2, L3	3 turn 1 mm spiral coil	D = 3.0 mm; 120 nH	
R1, R2	resistor	10 Ω	SMD 1206
R3	resistor	15 Ω	SMD 1206

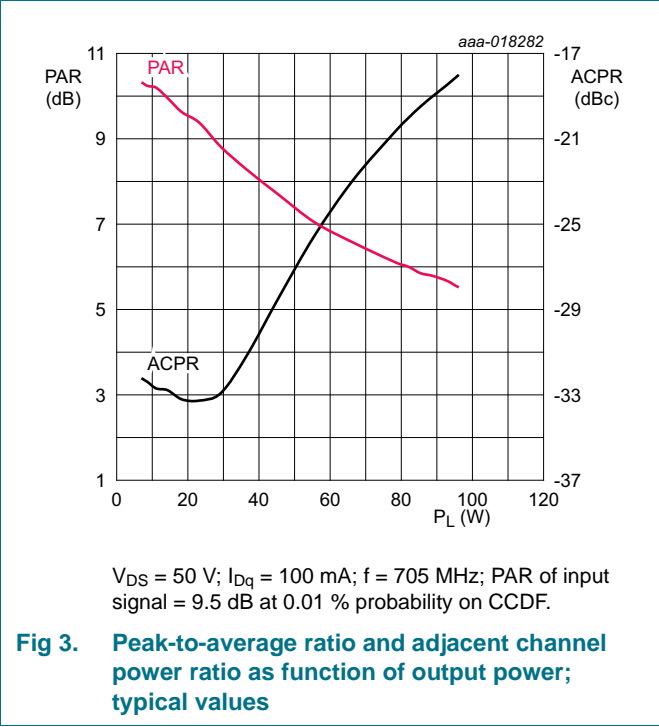
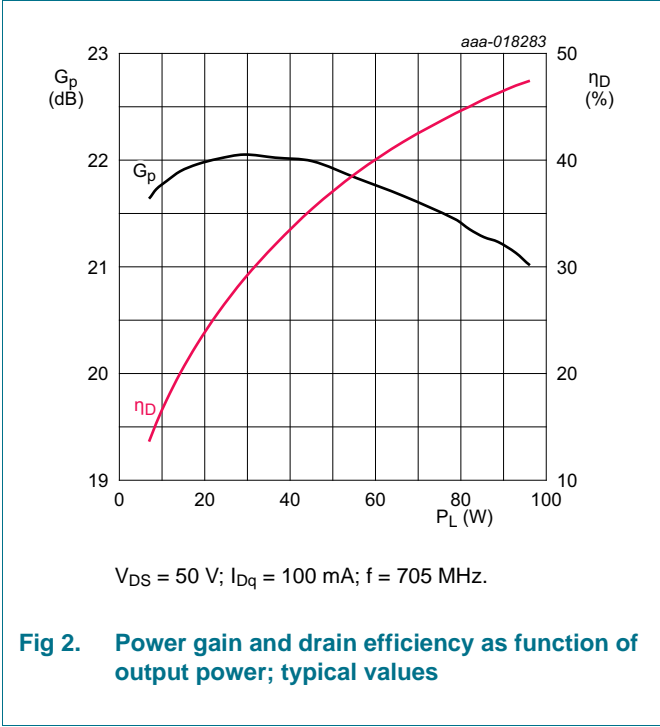
[1] American Technical Ceramics type 100B.

[2] American Technical Ceramics type 800A.

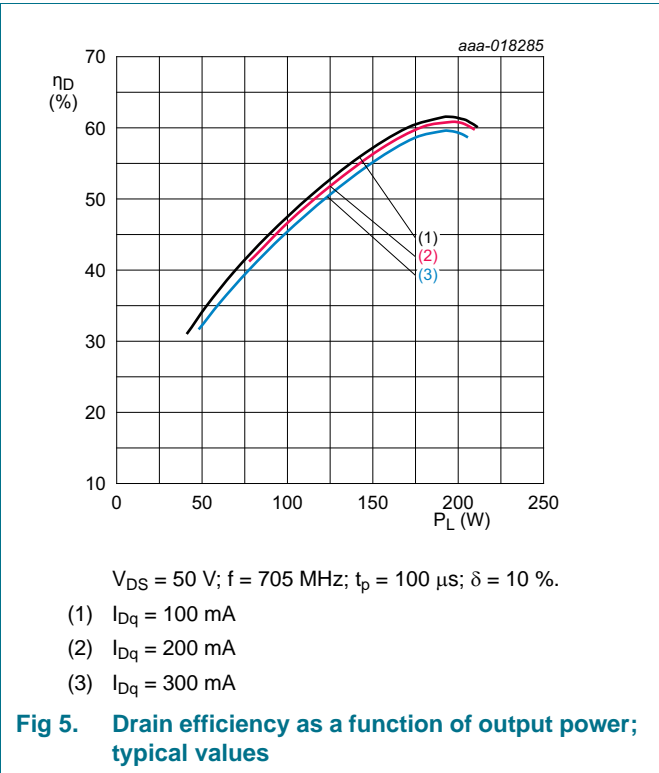
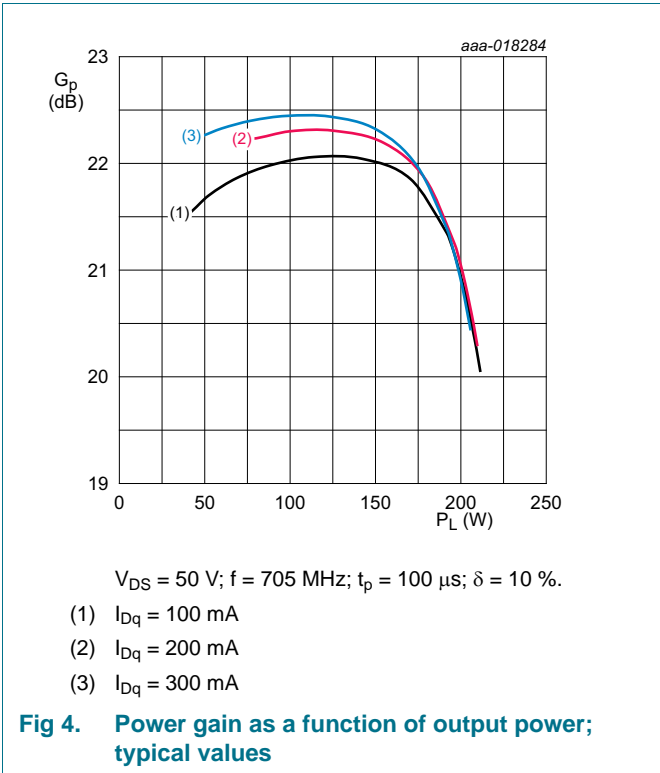
[3] American Technical Ceramics type 800B.

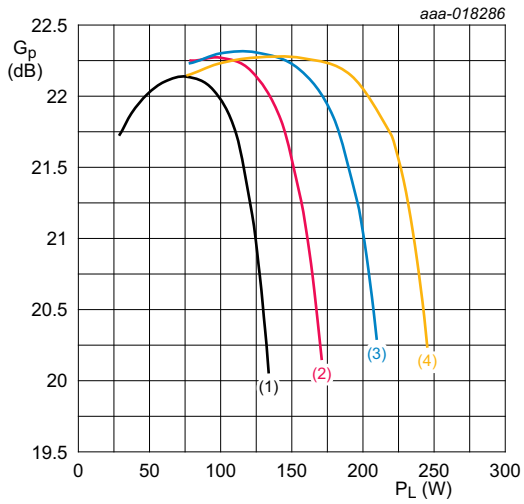
7.3 Graphical data

7.3.1 DVB-T



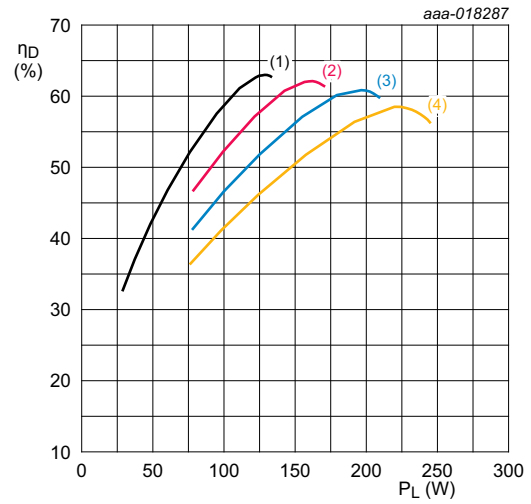
7.3.2 CW pulsed





- $I_{Dq} = 100 \text{ mA}$; $f = 705 \text{ MHz}$; $t_p = 100 \text{ }\mu\text{s}$; $\delta = 10 \text{ \%}$.
- (1) $V_{DS} = 40 \text{ V}$
 - (2) $V_{DS} = 45 \text{ V}$
 - (3) $V_{DS} = 50 \text{ V}$
 - (4) $V_{DS} = 55 \text{ V}$

Fig 6. Power gain as a function of output power; typical values



- $I_{Dq} = 100 \text{ mA}$; $f = 705 \text{ MHz}$; $t_p = 100 \text{ }\mu\text{s}$; $\delta = 10 \text{ \%}$.
- (1) $V_{DS} = 40 \text{ V}$
 - (2) $V_{DS} = 45 \text{ V}$
 - (3) $V_{DS} = 50 \text{ V}$
 - (4) $V_{DS} = 55 \text{ V}$

Fig 7. Drain efficiency as a function of output power; typical values

8. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT502A

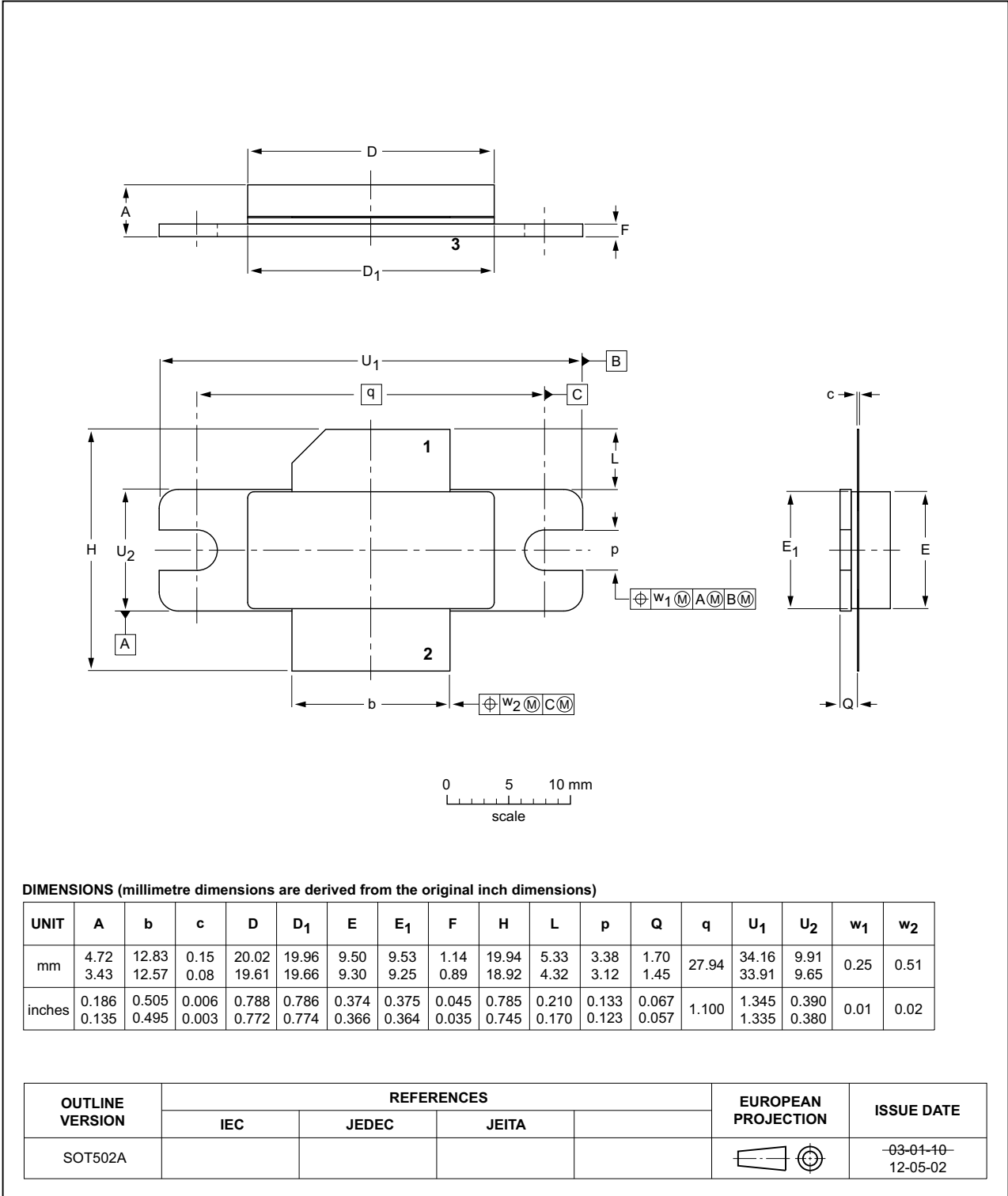


Fig 8. Package outline SOT502A

Earless flanged ceramic package; 2 leads

SOT502B

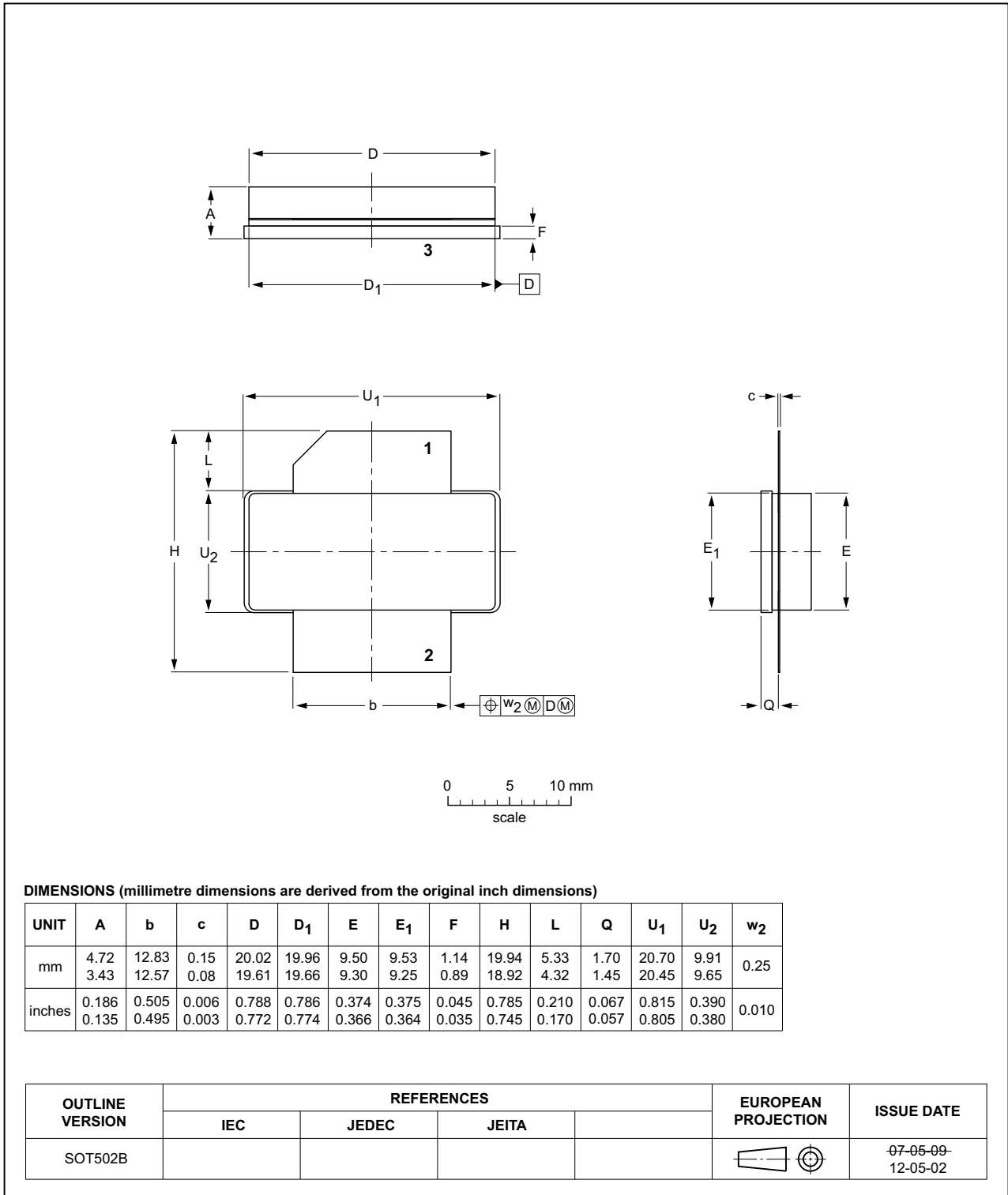


Fig 9. Package outline SOT502B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
ESD	ElectroStatic Discharge
DVB-T	Digital Video Broadcast - Terrestrial
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
UHF	Ultra High Frequency
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF882_BLF882S v.2	20150703	Product data sheet	-	BLF882_BLF882S v.1
Modifications:	<ul style="list-style-type: none"> • Table 1 on page 1: table updated • Table 5 on page 2: typical value added • Table 7 on page 3: typical values added • Table 8 on page 3: table updated • Section 7 on page 3: section expanded 			
BLF882_BLF882S v.1	20141219	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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